

## TCS1200

### 1200 Watts, 53 Volts Pulsed Avionics at 1030 MHz

#### **GENERAL DESCRIPTION**

The TCS1200 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems at 1030 MHz, with the pulse width and duty required for TCAS applications. The device has gold thin-film metalization and emitter ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

# CASE OUTLINE 55TU-1

#### ABSOLUTE MAXIMUM RATINGS

**Maximum Power Dissipation** 

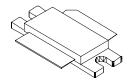
Device Dissipation @ 25°C<sup>1</sup> 2095 W

**Maximum Voltage and Current** 

Collector to Base Voltage ( $BV_{ces}$ ) 65 V Emitter to Base Voltage ( $BV_{ebo}$ ) 3.5 V Collector Current ( $I_c$ ) 60 A

**Maximum Temperatures** 

Storage Temperature -65 to +200 °C Operating Junction Temperature +200 °C



#### **ELECTRICAL CHARACTERISTICS @ 25°C**

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P <sub>out</sub>	Power Out	Pulse Width = 32μs	1200			W
$P_{g}$	Power Gain	Duty Factor = 2%	10.2			dB
$\eta_c$	Collector Efficiency	$F = 1030 \text{ MHz}, V_{cc} = 53 \text{ Volts}$	45			%
$R_L$	Return Loss	Pin = 115 Watts	-10			dB
Tr	Rise Time				100	ns
Pd	Pulse Droop				0.5	dB
VSWR	Load Mismatch Tolerance <sup>1</sup>		2.5:1			

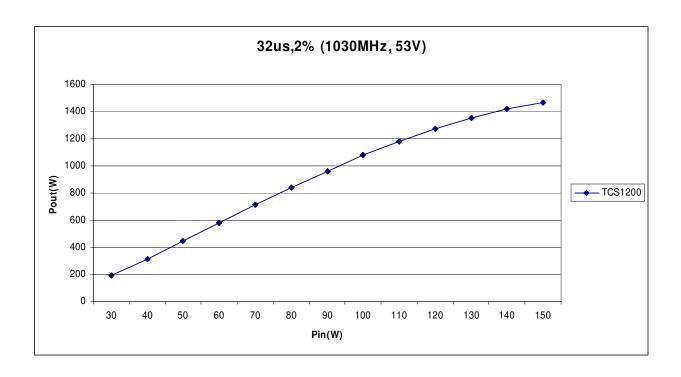
#### **FUNCTIONAL CHARACTERISTICS @ 25°C**

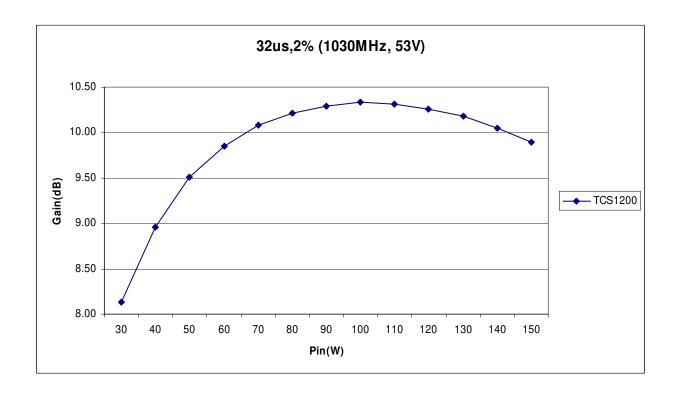
$BV_{ebo}$	Emitter to Base Breakdown	Ie = 40  mA	3.5		V
$BV_{ces}$	Collector to Emitter Breakdown	Ic = 100  mA	65		V
$h_{FE}$	DC – Current Gain	Vce = 5V, Ic = 1A	20		
θjc <sup>1</sup>	Thermal Resistance			0.012	°C/W

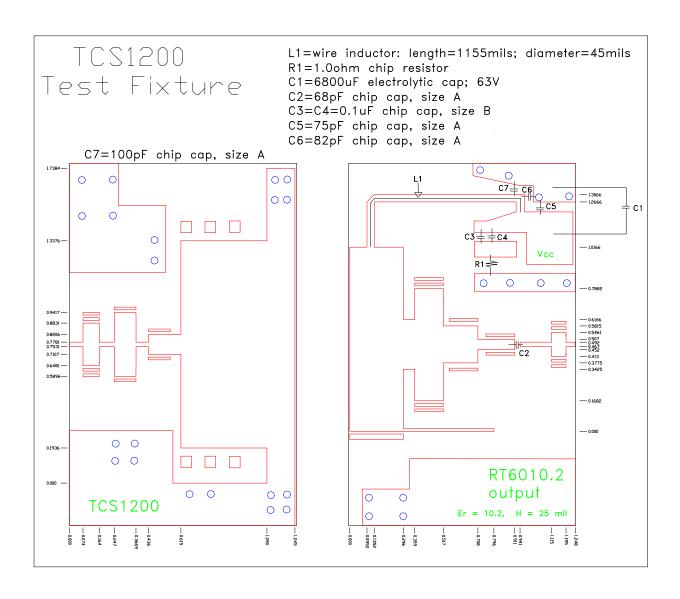
Rev B April, 2009

NOTES: 1. At rated output power and pulse conditions

2. See plots below for Mode S data at 50V as well as the standard 32us,2% data at 53V







#### Dimensions in inches

#### TCS1200

